

#### ABSTRACT OF THE DISCLOSURE

A semiconductor device and a fabricating method for the same are disclosed, in which when forming a capacitor sacrificial film pattern, even if a 5 misalignment occurs, the degradation of the dielectric property due to a direct contact between the contact plug and the dielectric medium can be prevented. The semiconductor device includes a connecting part connected through an insulating layer of a substrate 10 to a conductive layer, a seed separating layer formed around the connecting part and the insulating layer to provide an open region exposing at least part of the connecting part, a seed layer filled into the open region of the seed separating layer and a capacitor. 15 The capacitor includes of a lower electrode formed upon the seed layer, a dielectric medium formed upon the lower electrode, and an upper electrode formed upon the dielectric medium.